Abstract of the Disclosure:

An integrated, tunable capacitance is specified in which the quality factor is improved by virtue of the fact that, instead of source/drain regions, provision is made of highly doped well terminal regions having a deep depth, for example formed as collector deep implantation regions. This reduces the series resistance of the tunable capacitance. The integrated, tunable capacitance can be used for example in integrated voltage-controlled oscillator circuits in which a high quality factor is demanded.

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